

Appl. No. 10/601,121

**Amendments to the Specification:**

Please replace paragraph [0007] with the following amended paragraph:

[0007] Accordingly, there is a need to provide lateral power devices, such as MOSFETs and ~~bipolar~~ bipolar devices, with reduced parasitic resistance of interconnects to reduce on-state resistance. In the case of MOSFETs, there is also a need for fabricating lateral power MOSFETs using fewer processing steps than conventionally used.

Please replace paragraph [0014] with the following amended paragraph:

[0014] Yet further, in another preferred embodiment of the invention a self-aligned ~~silicide~~ silicide is formed over the source, drain and gate of the transistor.